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April 2001

FDC645N

N-Channel PowerTrench[®] MOSFET

General Description

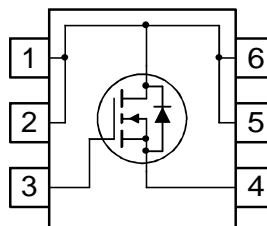
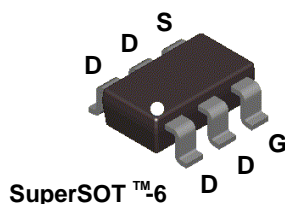
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

Applications

- DC/DC converter

Features

- 5.5 A, 30 V. $R_{DS(ON)} = 30\text{ m}\Omega$ @ $V_{GS} = 4.5\text{ V}$
 $R_{DS(ON)} = 26\text{ m}\Omega$ @ $V_{GS} = 10\text{ V}$
- High performance trench technology for extremely low $R_{DS(ON)}$
- Low gate charge (13 nC typical)
- High power and current handling capability



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Drain Current – Continuous (Note 1a)	5.5	A
	– Pulsed	20	
P_D	Maximum Power Dissipation (Note 1a) (Note 1b)	1.6	W
		0.8	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	30	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.645	FDC645N	7"	8mm	3000 units

Electrical Characteristics T_A = 25°C unless otherwise noted						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
$\frac{\Delta B_{V_{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = 12 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = -12 V, V _{DS} = 0 V			-100	nA
On Characteristics (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	0.8	1.4	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		-4		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 4.5 V, I _D = 5.5 A V _{GS} = 10 V, I _D = 6.2 A V _{GS} = 4.5 V, I _D = 5.5 A, T _J = 125°C		25 23 34	30 26 48	mΩ
I _{D(on)}	On-State Drain Current	V _{GS} = 4.5 V, V _{DS} = 5 V	20			A
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 5.5 A		33		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0 V, f = 1.0 MHz		1460		pF
C _{oss}	Output Capacitance			227		pF
C _{riss}	Reverse Transfer Capacitance			96		pF
Switching Characteristics (Note 2)						
t _{d(on)}	Turn-On Delay Time	V _{DS} = 15 V, I _D = 1 A, V _{GS} = 4.5 V, R _{GEN} = 6 Ω		8	16	ns
t _r	Turn-On Rise Time			9	18	ns
t _{d(off)}	Turn-Off Delay Time			35	56	ns
t _f	Turn-Off Fall Time			7	14	ns
Q _g	Total Gate Charge	V _{DS} = 15 V, I _D = 6.2 A, V _{GS} = 4.5 V		13	21	nC
Q _{gs}	Gate-Source Charge			3.6		nC
Q _{gd}	Gate-Drain Charge			3.6		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current				1.3	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.3 A (Note 2)		0.7	1.2	V

Notes:

- R_{θJA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.
 - 78°C/W when mounted on a 1in² pad of 2oz copper on FR-4 board.
 - 156°C/W when mounted on a minimum pad.
- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Typical Characteristics

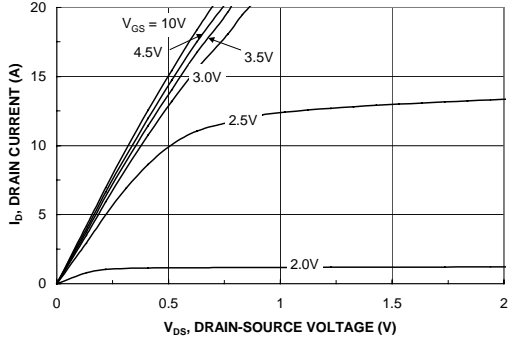


Figure 1. On-Region Characteristics.

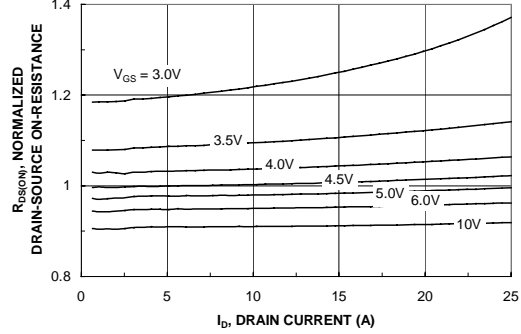


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

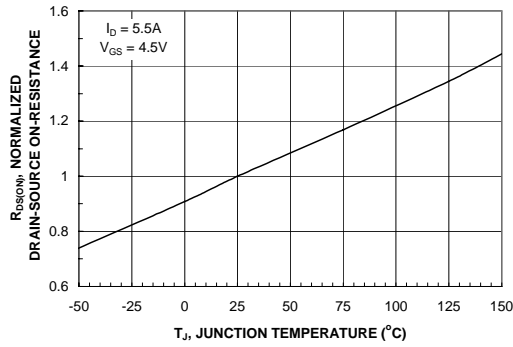


Figure 3. On-Resistance Variation with Temperature.

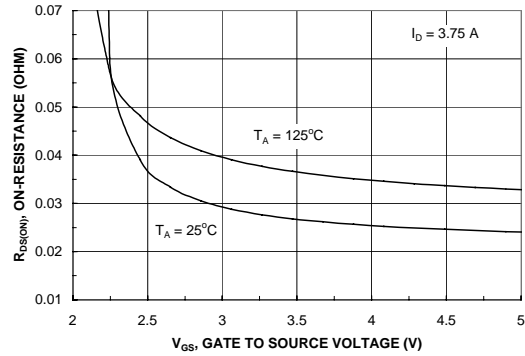


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

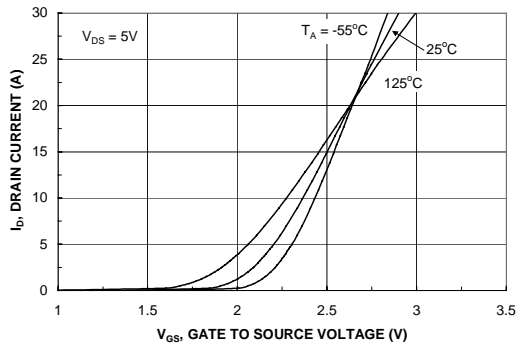


Figure 5. Transfer Characteristics.

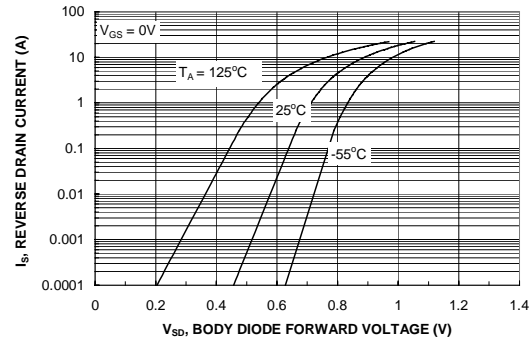


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

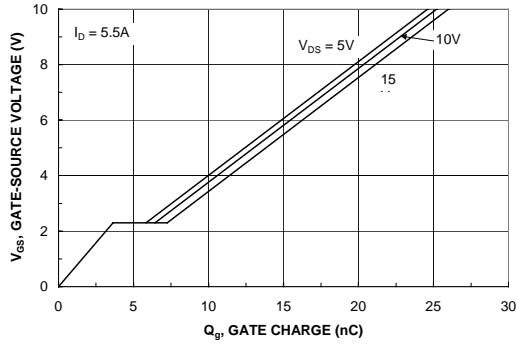


Figure 7. Gate Charge Characteristics.

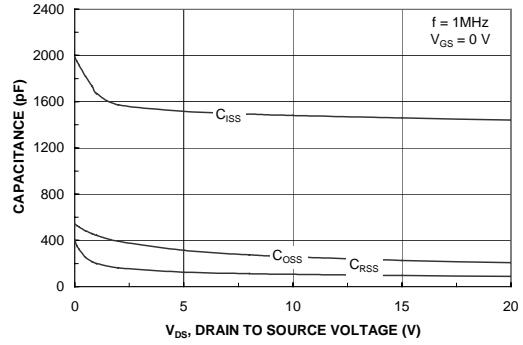


Figure 8. Capacitance Characteristics.

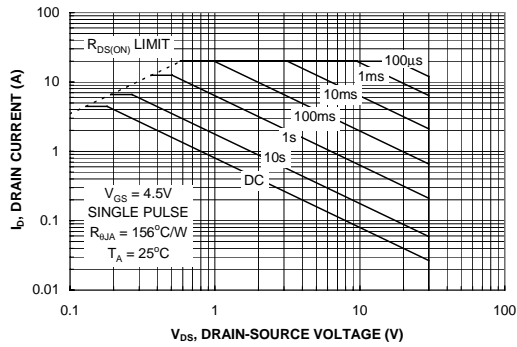


Figure 9. Maximum Safe Operating Area.

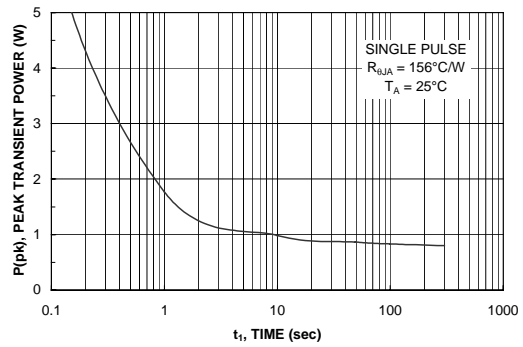


Figure 10. Single Pulse Maximum Power Dissipation.

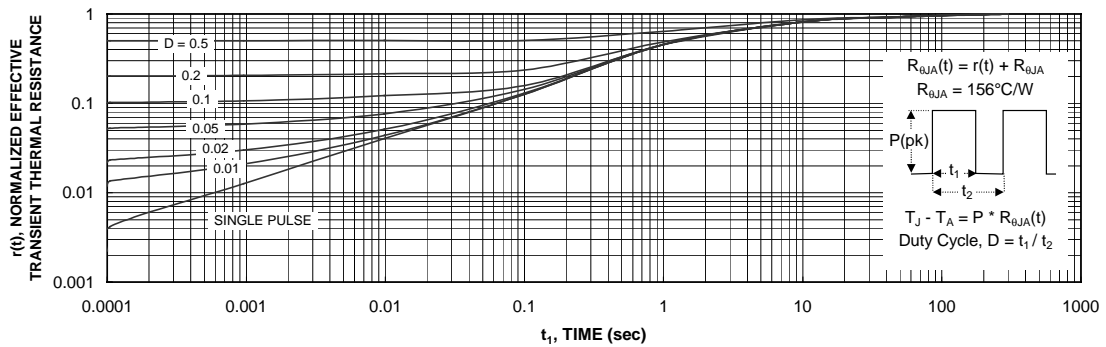


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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